

FH3011D

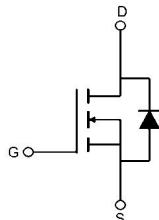
N-Channel Trench Power MOSFET

Features

- 30V,8.5A
- $R_{DS(ON)} < 22m\Omega$ @ $V_{GS} = 10V$
- $R_{DS(ON)} < 35m\Omega$ @ $V_{GS} = 4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

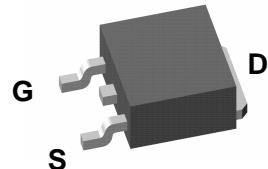
- Load Switch
- PWM Application
- Power management



Schematic diagram



Marking and pin assignment



TO-252 top view

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	A
		$T_A = 100^\circ C$	A
I_{DM}	Pulsed Drain Current ^{note1}	34	A
P_D	Power Dissipation	$T_A = 25^\circ C$	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	1.87	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=30\text{V}$, $V_{\text{GS}}=0\text{V}$,	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{\text{DS}}=0\text{V}$, $V_{\text{GS}}=\pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_D=250\mu\text{A}$	1.0	1.5	2.5	V
$R_{\text{DS}(\text{on})}$ note2	Static Drain-Source on-Resistance	$V_{\text{GS}}=10\text{V}$, $I_D=8.5\text{A}$	-	16	22	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}$, $I_D=5\text{A}$	-	25	35	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{\text{DS}}=15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1.0\text{MHz}$	-	790	-	pF
C_{oss}	Output Capacitance		-	79	-	pF
C_{rss}	Reverse Transfer Capacitance		-	61	-	pF
Q_g	Total Gate Charge	$V_{\text{DS}}=15\text{V}$, $I_D=5.8\text{A}$, $V_{\text{GS}}=10\text{V}$	-	5.2	-	nC
Q_{gs}	Gate-Source Charge		-	0.9	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	1.3	-	nC
Switching Characteristics						
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DS}}=15\text{V}$, $I_D=3\text{A}$, $R_{\text{GEN}}=3\Omega$, $V_{\text{GS}}=10\text{V}$	-	4.5	-	ns
t_r	Turn-on Rise Time		-	2.5	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time		-	14.5	-	ns
t_f	Turn-off Fall Time		-	3.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_s	Maximum Continuous Drain to Source Diode Forward Current		-	-	8.5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	34	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{\text{GS}}=0\text{V}$, $I_s=5\text{A}$	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Figure 1: Output Characteristics

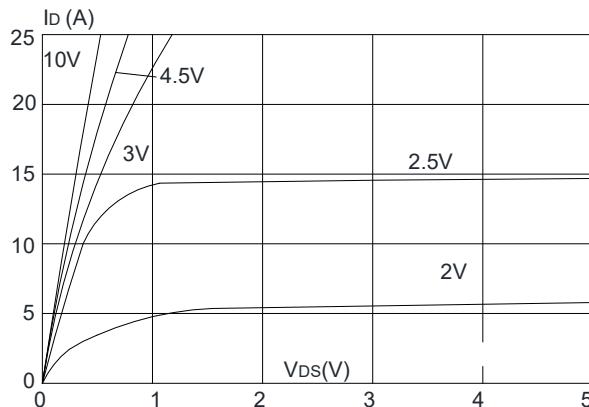


Figure 3: On-resistance vs. Drain Current

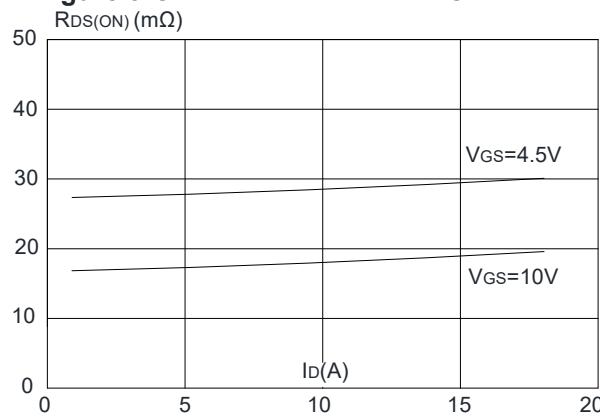


Figure 5: Gate Charge Characteristics

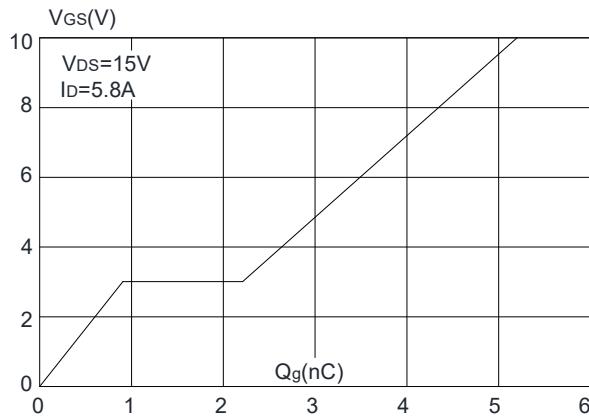


Figure 2: Typical Transfer Characteristics

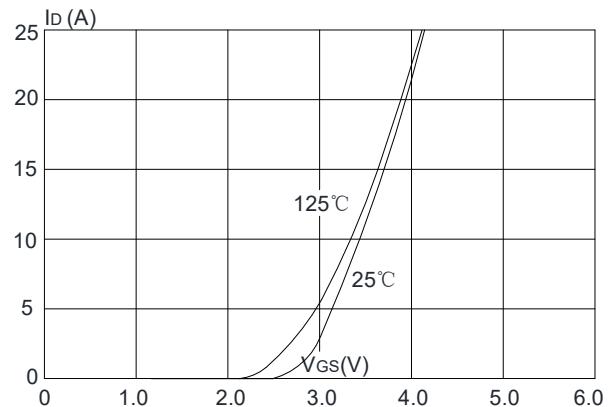


Figure 4: Body Diode Characteristics

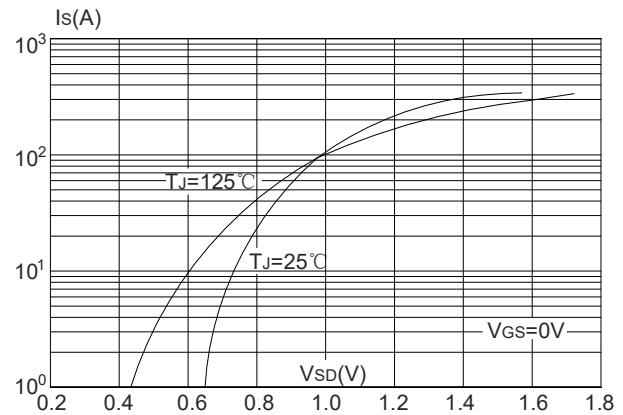


Figure 6: Capacitance Characteristics

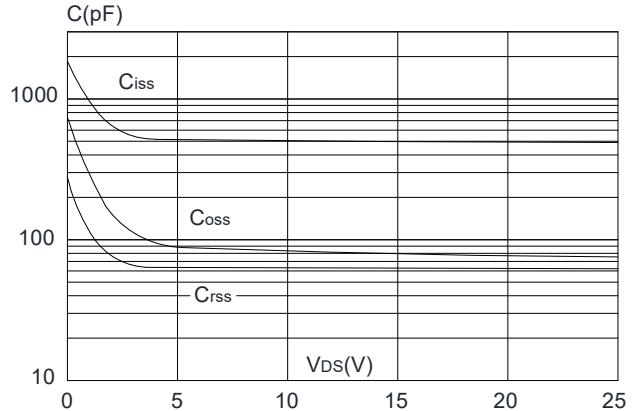


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

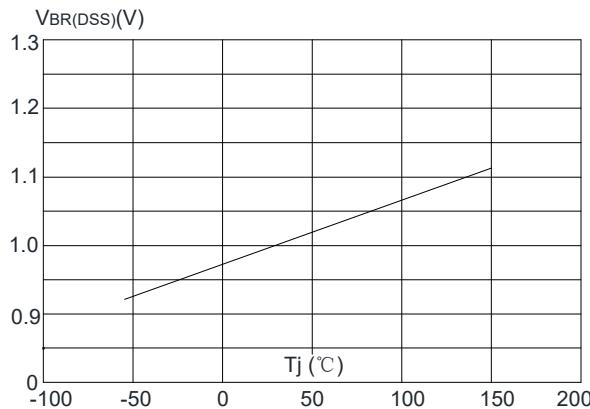


Figure 9: Maximum Safe Operating Area

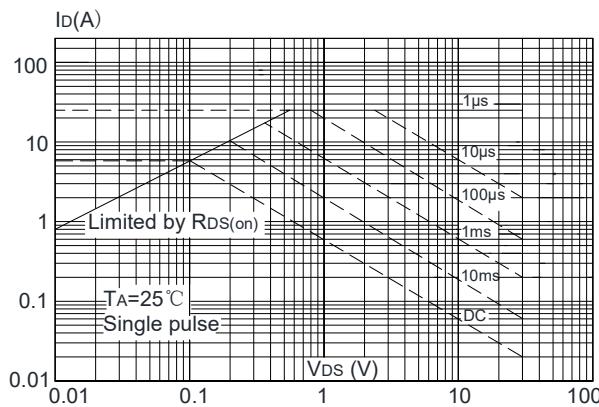


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

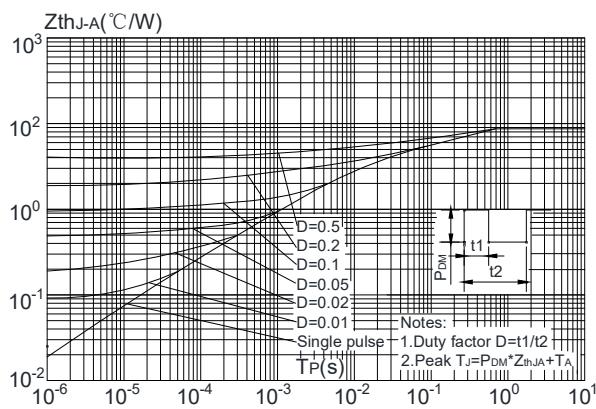


Figure 8: Normalized on Resistance vs. Junction Temperature

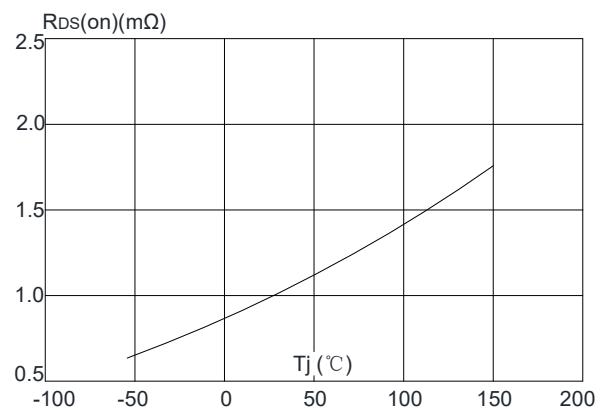
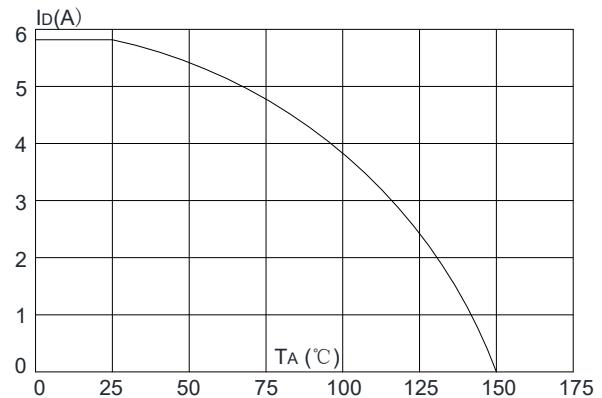


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature



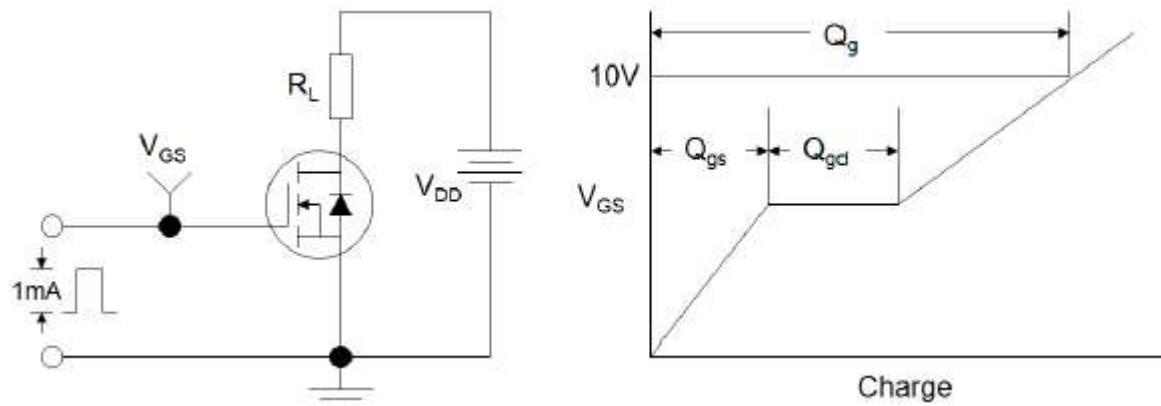
Test Circuit

Figure 1: Gate Charge Test Circuit & Waveform

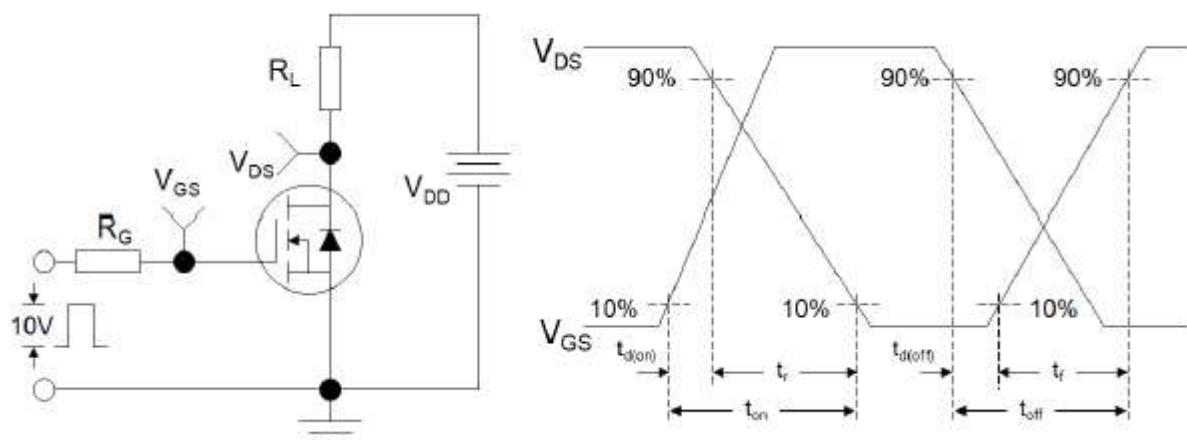


Figure 2: Resistive Switching Test Circuit & Waveforms

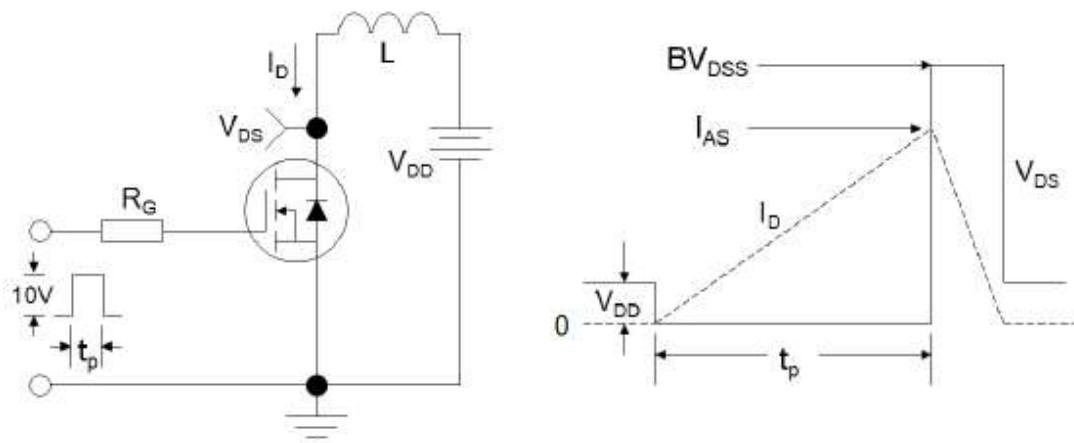
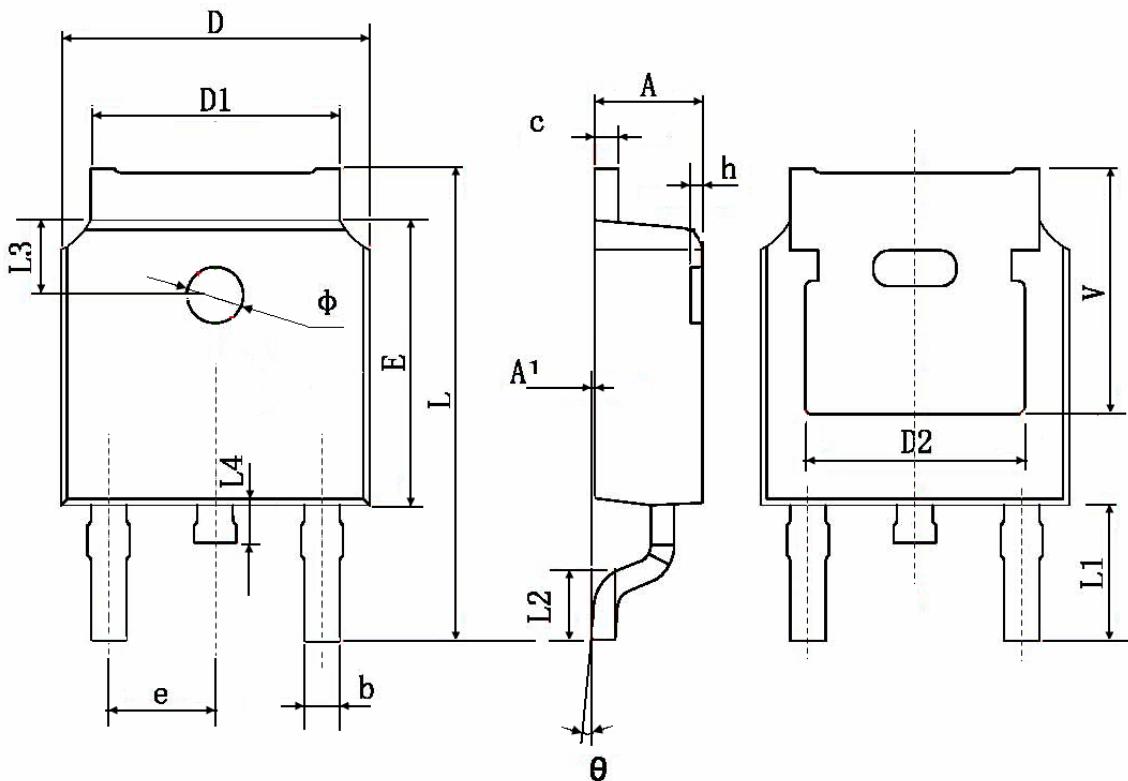


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

Package Information : TO-252



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	